30V, N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD17501Q5A

FEATURES

- **Ultralow Q_g and Q_{gd}**
- **Low Thermal Resistance**
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- **SON 5-mm × 6-mm Plastic Package**

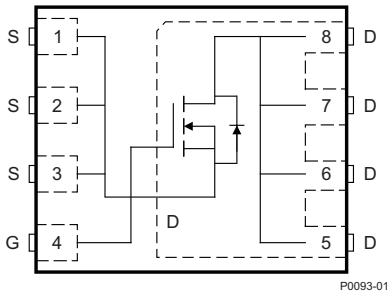
APPLICATIONS

- **Point-of-Load Synchronous Buck in Networking, Telecom, and Computing Systems**
- **Optimized for Synchronous FET Applications**

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.

Top View



PRODUCT SUMMARY

T_A = 25°C unless otherwise stated		TYPICAL VALUE		UNIT
V_{DS}	Drain to Source Voltage	30		V
Q_g	Gate Charge Total (4.5V)	13.2		nC
Q_{gd}	Gate Charge Gate to Drain	3.5		nC
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 4.5V	3	mΩ
		V_{GS} = 10V	2.4	mΩ
$V_{GS(th)}$	Threshold Voltage	1.3		V

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD17501Q5A	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

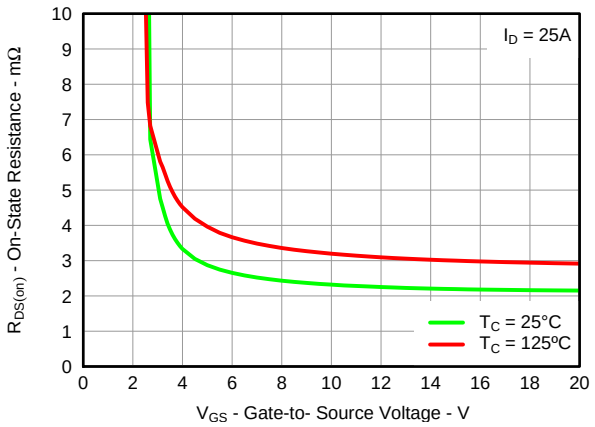
ABSOLUTE MAXIMUM RATINGS

T_A = 25°C unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Continuous Drain Current, T_C = 25°C	100	A
	Continuous Drain Current(1)	28	A
I_{DM}	Pulsed Drain Current, T_A = 25°C(2)	187	A
P_D	Power Dissipation(1)	3.2	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, single pulse I_D = 90A, L = 0.1mH, R_G = 25Ω	405	mJ

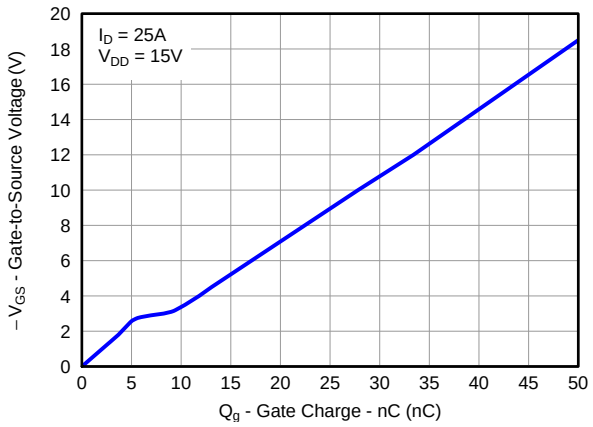
(1) Typical $R_{\theta JA}$ = 39°C/W on a 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration ≤300μs, duty cycle ≤2%

$R_{DS(on)}$ vs V_{GS}



GATE CHARGE



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NexFET is a trademark of Texas Instruments.

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

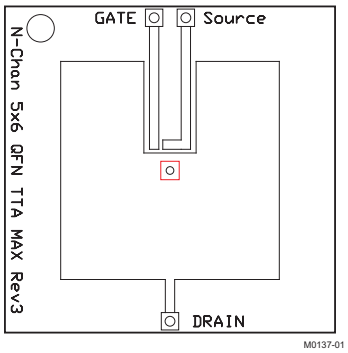
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	V_{GS} = 0V, I_{DS} = 250μA	30			V
I_{DSS}	Drain to Source Leakage Current	V_{GS} = 0V, V_{DS} = 24V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{DS} = 0V, V_{GS} = 20V			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_{DS} = 250μA	1	1.3	1.8	V
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 4.5V, I_{DS} = 25A		3	3.7	mΩ
		V_{GS} = 10V, I_{DS} = 25A		2.4	2.9	mΩ
g_{fs}	Transconductance	V_{DS} = 15V, I_{DS} = 25A		110		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		2040	2630	pF
C_{oss}	Output Capacitance			1350	1700	pF
C_{rss}	Reverse Transfer Capacitance			66	85	pF
R_G	Series Gate Resistance			1.3	2.6	Ω
Q_g	Gate Charge Total (4.5V)	V_{DS} = 15V, I_{DS} = 25A		13.2	17	nC
Q_{gd}	Gate Charge Gate to Drain			3.5		nC
Q_{gs}	Gate Charge Gate to Source			5.4		nC
$Q_{g(th)}$	Gate Charge at Vth			2.9		nC
Q_{oss}	Output Charge	V_{DS} = 13.7V, V_{GS} = 0V		35		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 15V, V_{GS} = 4.5V, I_{DS} = 25A, R_G = 2Ω		10.4		ns
t_r	Rise Time			17		ns
$t_{d(off)}$	Turn Off Delay Time			18		ns
t_f	Fall Time			7.9		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_{SD} = 25A, V_{GS} = 0V		0.8	1	V
Q_{rr}	Reverse Recovery Charge	V_{DD} = 13.7V, I_F = 25A, di/dt = 300A/μs		46		nC
t_{rr}	Reverse Recovery Time			32		ns

THERMAL CHARACTERISTICS

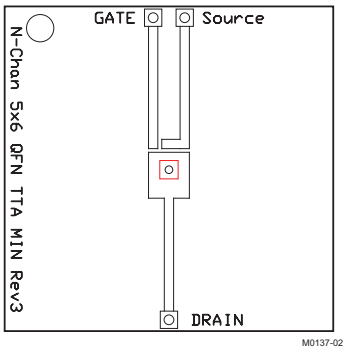
(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case(1)			1	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient(1)(2)			49	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 49°C/W when mounted on 1 inch^2 (6.45 cm^2) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 114°C/W when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

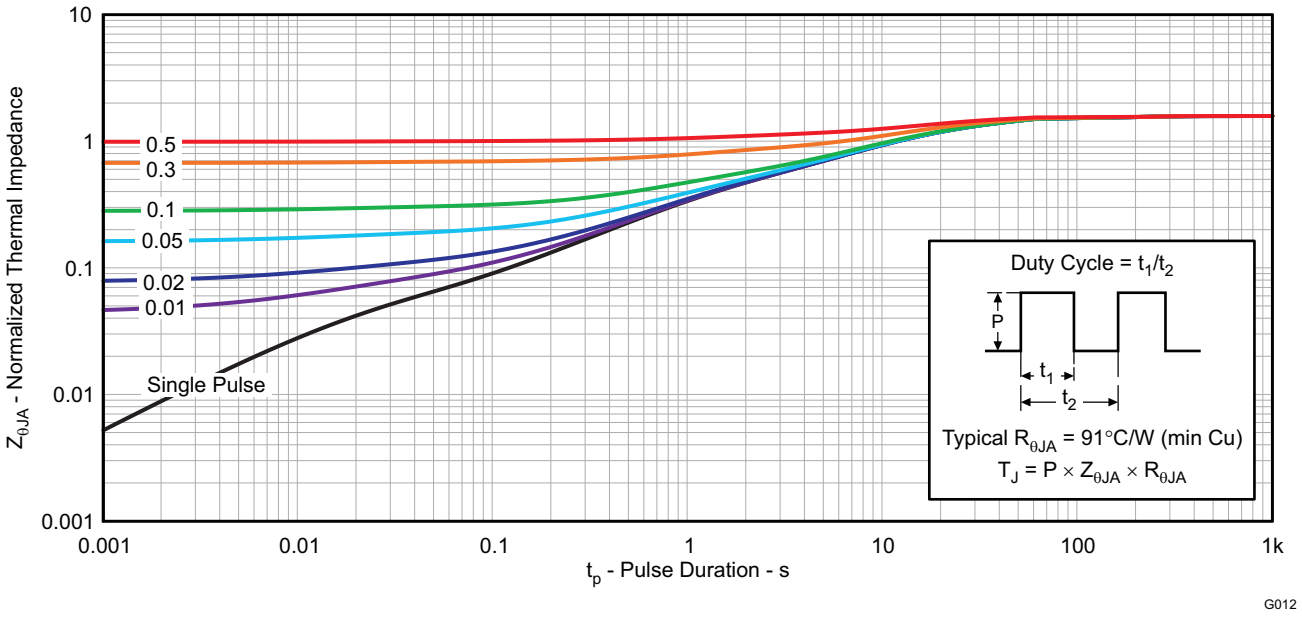


Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

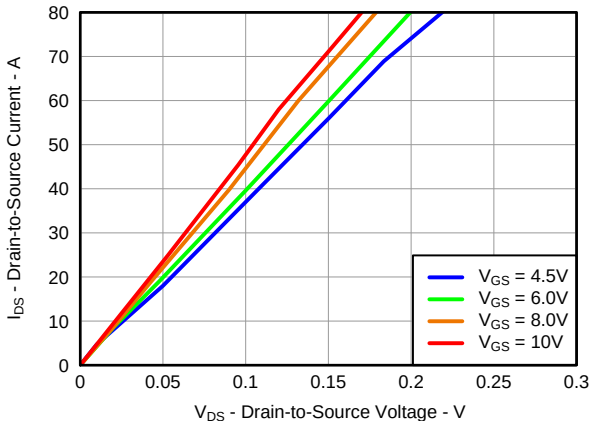


Figure 2. Saturation Characteristics

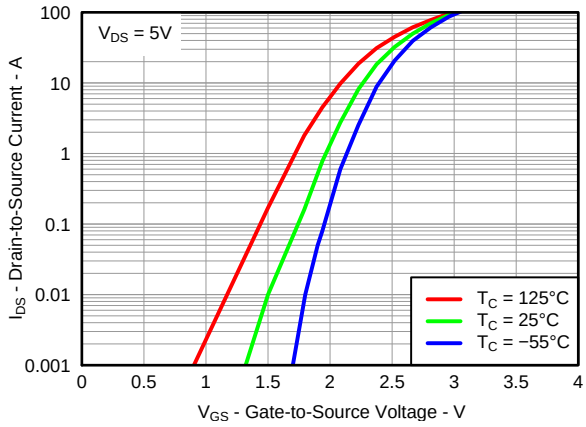


Figure 3. Transfer Characteristics

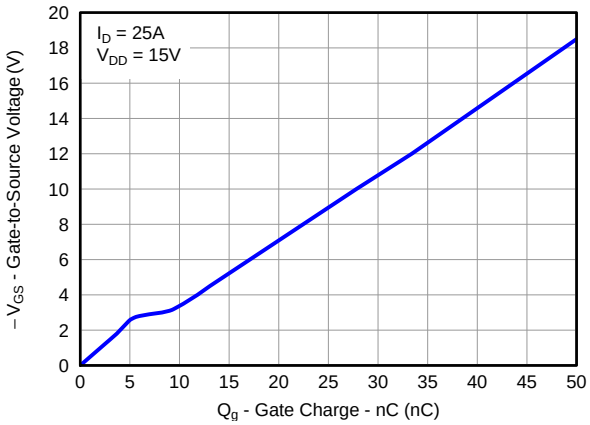


Figure 4. Gate Charge

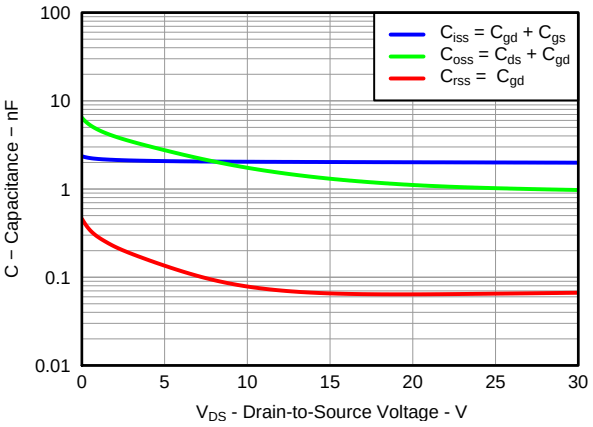


Figure 5. Capacitance

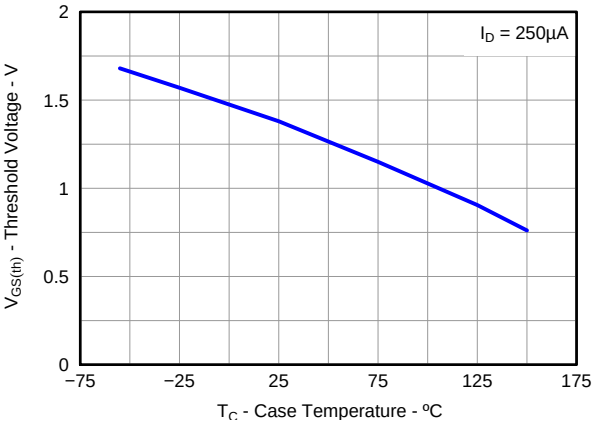


Figure 6. Threshold Voltage vs. Temperature

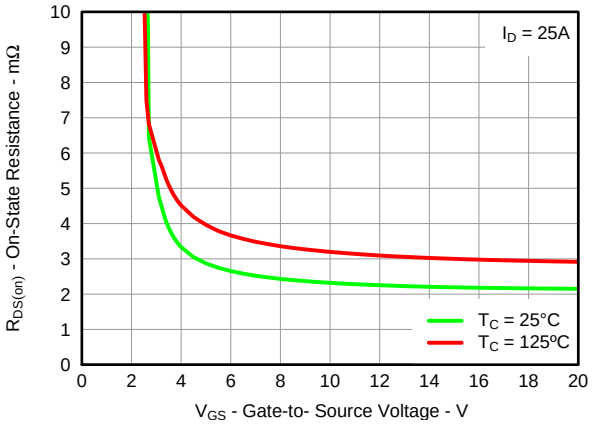


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

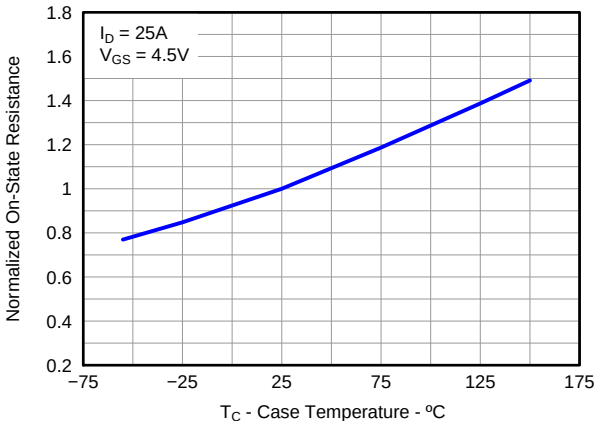


Figure 8. Normalized On-State Resistance vs. Temperature

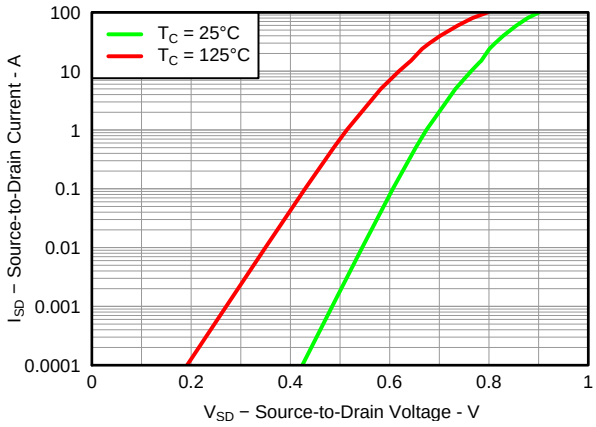


Figure 9. Typical Diode Forward Voltage

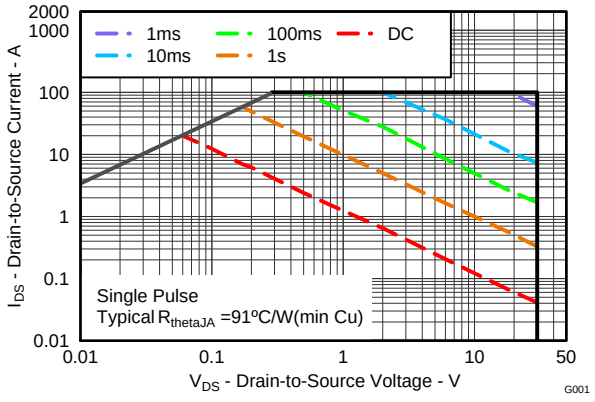


Figure 10. Maximum Safe Operating Area

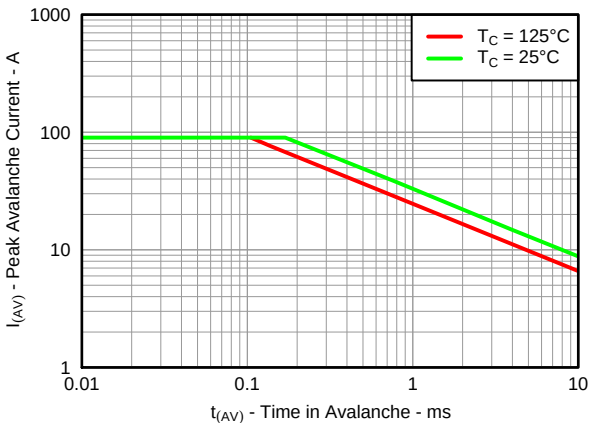


Figure 11. Single Pulse Unclamped Inductive Switching

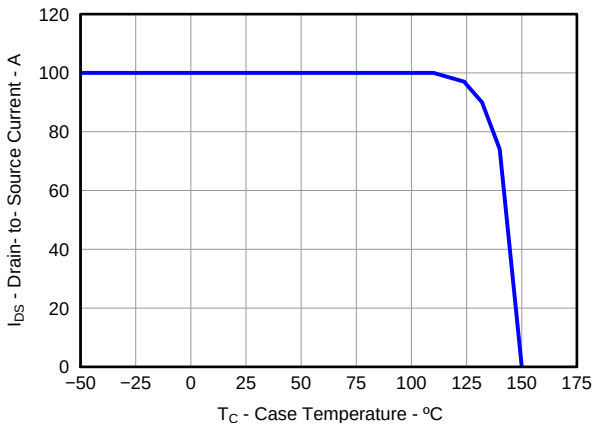
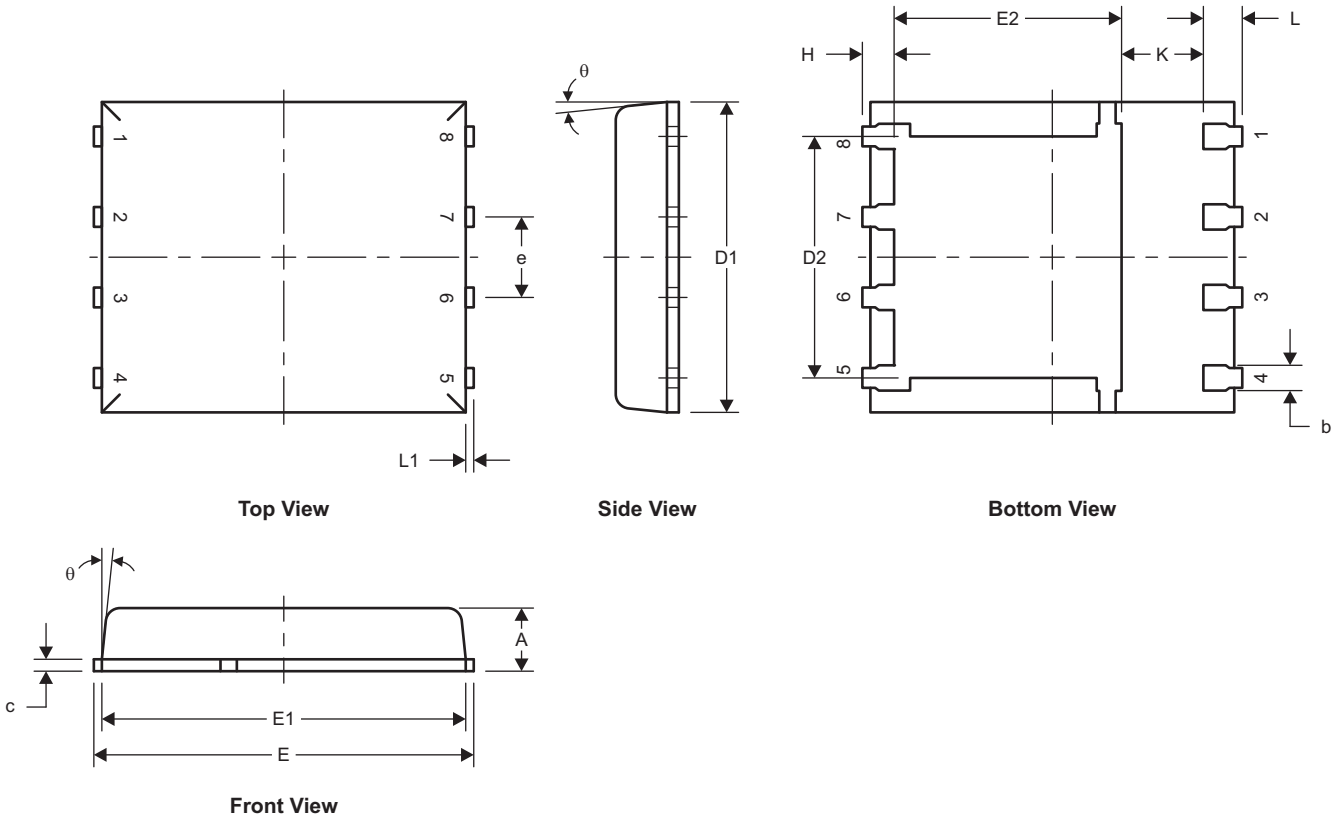


Figure 12. Maximum Drain Current vs. Temperature

MECHANICAL DATA

Q5A Package Dimensions



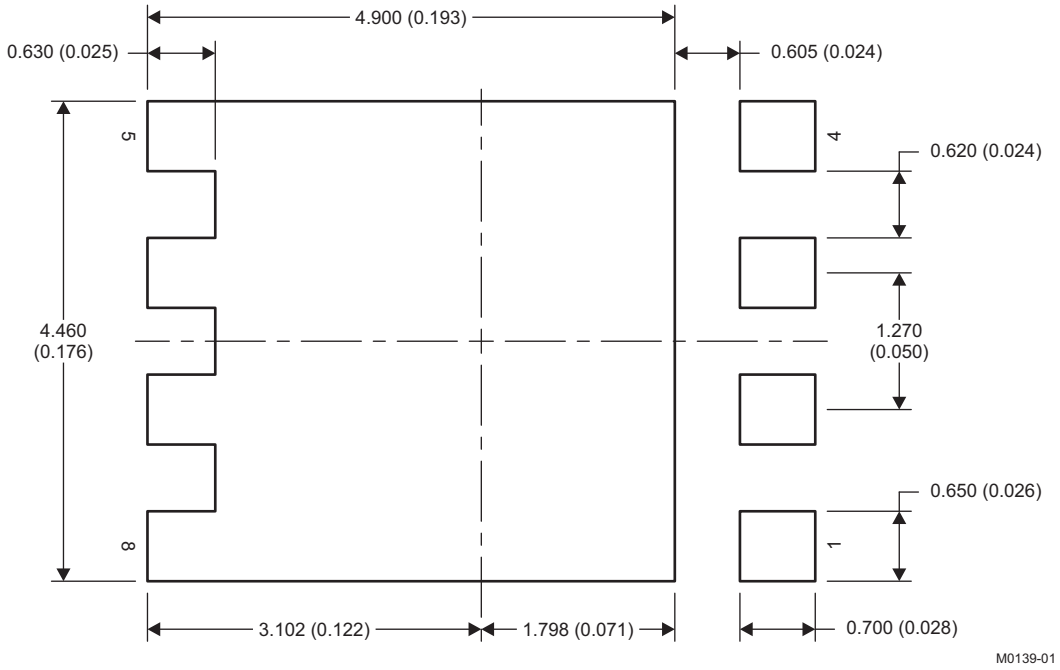
Top View **Side View** **Bottom View**

Front View

M0135-01

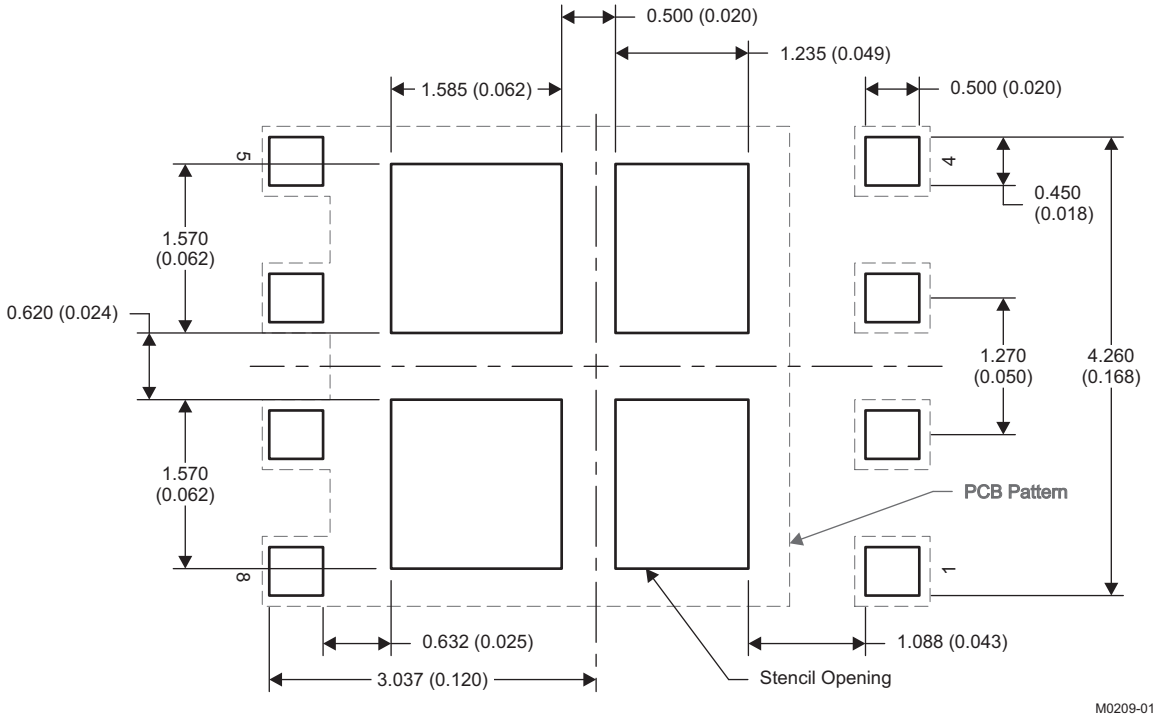
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.41	0.51
c	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.17	1.27	1.37
H	0.41	0.56	0.71
K	1.10		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°		12°

Recommended PCB Pattern



NOTE: Dimensions are in mm (inches).

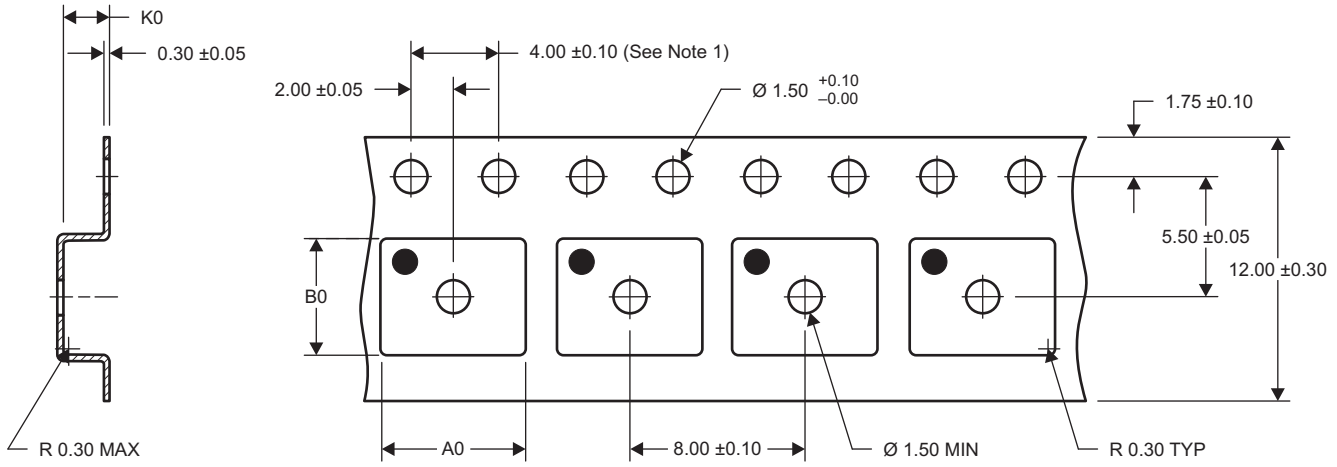
Stencil Recommendation



NOTE: Dimensions are in mm (inches).

For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

Q5A Tape and Reel Information



A0 = 6.50 ±0.10
B0 = 5.30 ±0.10
K0 = 1.40 ±0.10

M0138-01

NOTES: 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified)
5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

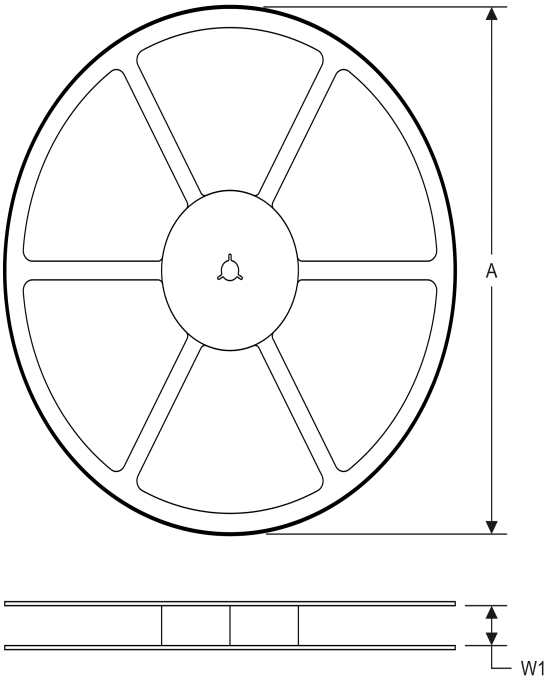
REVISION HISTORY

Changes from Original (December 2010) to Revision A	Page
• Changed V_{GS} in the Abs Max Ratings table From: +20/-12V To: ±20V	1
• Changed the I_{GSS} Test Conditions From: V_{GS} = 20V +20/-12 To:V_{GS} = 20 V	2

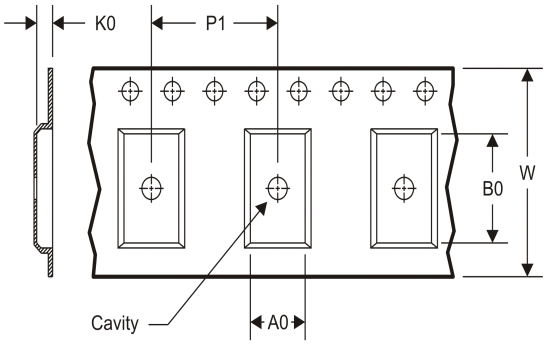
Changes from Revision A (July 2011) to Revision B	Page
• Changed Figure 10	5

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



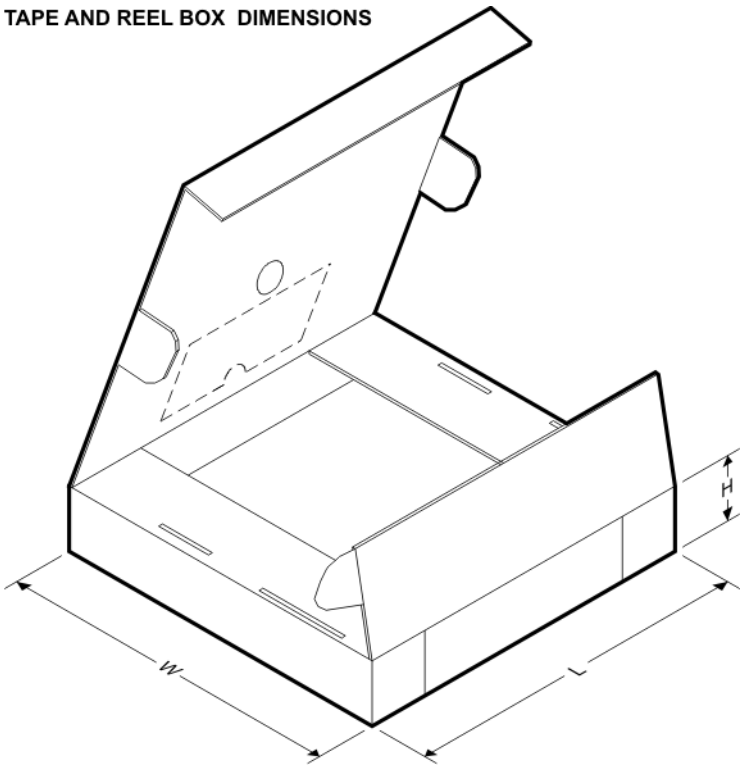
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17501Q5A	SON	DQJ	8	2500	330.2	12.4	6.5	5.3	1.4	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD17501Q5A	SON	DQJ	8	2500	347.0	342.0	55.0

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